# 2SC1953

# Silicon NPN epitaxial planar type

For audio system/pre-drive Complementary to 2SA0914

## ■ Features

- ullet High collector-emitter voltage (Base open)  $V_{\text{CEO}}$
- $\bullet$  Small collector output capacitance (Common base, input open circuited)  $C_{ob}$
- A complementary pair with 2SA0914, is optimum for the pre-driver stage of a 60 W to 100 W output amplifier
- TO-126B package which requires no insulation plate for installation to the heat sink

# ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	150	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	150	V	
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	5	V	
Collector current	$I_{C}$	50	mA	
Peak collector current	I <sub>CP</sub>	100	mA	
Collector power dissipation	$P_{C}$		W	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C 、	

# 0.75±0.1 0.5±0.1 0.5±0.1 0.5±0.1 0.5±0.1 0.5±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1 1.76±0.1

### Electrical Characteristics T<sub>a</sub> = 25°C ± 3°C

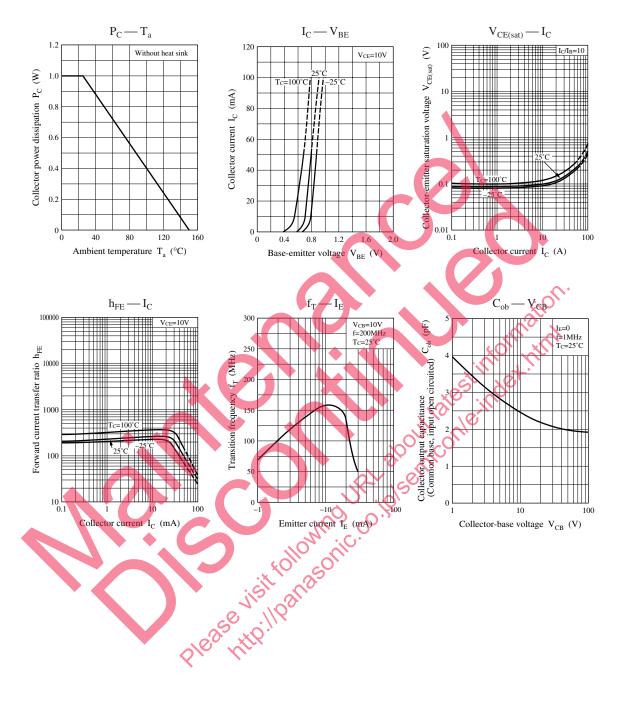
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 100 \mu$ A, $I_B = 0$	150			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10  \mu A, I_{\rm C} = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 100 \text{ V}, I_E = 0$			1	μΑ
Forward current transfer ratio *	ChFE	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$	130		330	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 30 \text{ mA}, I_B = 3 \text{ mA}$			1	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$	70			MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$			3	pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## 2. \*: Rank classification

Rank	Q	R
$h_{FE}$	130 to 220	185 to 330

10 Collector-base voltage  $V_{CB}$  (V)



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